

ABSTRACT OF THE DISCLOSURE

A semiconductor light emitting device includes:
a silicon substrate; and a plurality of column-shaped
5 multilayered structures formed on the silicon substrate
in such a manner that the column-shaped multilayered
structures are insulated from one another, the
column-shaped multilayered structures being made of a
nitride semiconductor material, and each column-shaped
10 multilayered structure including a light emitting layer,
wherein the column-shaped multilayered structures are
connected to one another by an electrode.